Claims

1. A method for cleaning a chamber, comprising:

introducing a gas to a processing volume of the chamber;

providing a first radio frequency (RF) power having a first frequency of 40 MHz or greater to a lid of the chamber;

providing a second RF power having a second frequency to an electrode disposed in a substrate support within the processing volume, wherein the second frequency is 10 MHz to 20 MHz; and

removing at least a portion of a film disposed on a surface of a chamber component of the chamber.

2. The method of claim 1, wherein the gas is an oxygen-containing gas.

3. The method of claim 1, wherein providing the first RF power comprises providing 1 kW to 3 kW of RF power.

4. The method of claim 1, wherein providing the second RF power comprises providing 1500 W to 6000 W of RF power to the electrode.

5. The method of claim 1, wherein a distance from an upper surface of the substrate support to an uppermost inner surface of the lid of the chamber is 2.54 cm to 38.1 cm.

6. The method of claim 5, wherein the distance is 12.7 cm to 15.24 cm.

7. The method of claim 1, wherein the first RF ionizes the gas in the processing volume of the chamber.

8. The method of claim 7, wherein the first RF is configured to clean an upper portion of the chamber.

9. The method of claim 1, wherein the second frequency is provided from a combination of a first frequency generator and a second frequency generator.

10. The method of claim 9, wherein the first frequency generator provides a frequency of 2 MHz.

11. The method of claim 9, wherein the second frequency generator provides a frequency of 13.56 MHz.

12. The method of claim 1, wherein a pressure within the processing volume is less than 50 mTorr during the removing.

13. The method of claim 1, wherein a pressure within the processing volume is 0.5 mTorr to 10 Torr.

14. A method for cleaning a chamber, comprising:

introducing an oxygen-containing gas to a processing volume of the chamber that has a substrate support therein;

regulating a pressure within the processing volume by a pump;

providing a first radio frequency (RF) power having a first frequency of 40 MHz or greater to a lid of the chamber;

removing at least a portion of a film disposed on a surface of a chamber component of the chamber.

15. The method of claim 14, wherein a pressure within the processing volume is less than 50 mTorr during the removing.

16. The method of claim 14, wherein a pressure within the processing volume is 0.5 mTorr to 10 Torr.

17. The method of claim 14, wherein a distance from an upper surface of the substrate support to an uppermost inner surface of the lid of the chamber is 2.54 cm to 38.1 cm.

18. The method of claim 17, wherein the distance is 12.7 cm to 15.24 cm.

19. A method for cleaning a chamber, comprising:

introducing an oxygen-containing gas to a processing volume of the chamber;

regulating a pressure within the processing volume by a pump;

providing a first radio frequency (RF) power having a first frequency of 40 MHz or greater to a lid of the chamber;

providing a second RF power having a second frequency to an electrode disposed in the processing volume, wherein the second frequency is a combination of a first frequency generator providing a frequency of 2 MHz and a second frequency generator providing a frequency of 13.56 MHz;

removing at least a portion of a film disposed on a surface of a chamber component of the chamber.

20. The method of claim 19, wherein the first RF power comprises providing 1 kW to 3 kW of RF power and the second RF power comprises providing 1500 W to 6000 W of RF power to the electrode.